

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((etch\$4 adj gas) and ((liquid adj crystal) and expos\$4 and (photoresist adj pattern) and pass\$4).dm.	US-PGPUB	OR	ON	2008/04/15 09:09
L2	8	(etch\$4 and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and pass\$4).dm.	US-PGPUB	OR	ON	2008/04/15 09:10
L3	20	(etch\$4 and (liquid adj crystal) and expos\$4 and photoresist and pattern and pass\$4).dm.	US-PGPUB	OR	ON	2008/04/15 09:11
L4	205	(etch\$4 and (liquid adj crystal) and expos\$4 and photoresist and pattern).dm.	US-PGPUB	OR	ON	2008/04/15 09:23
L5	6	((etch\$4 adj gas) and ((liquid adj crystal) and expos\$4 and photoresist and pattern).dm.	US-PGPUB	OR	ON	2008/04/15 09:26
L6	12	((etch\$4 near10 gas) and ((liquid adj crystal) and expos\$4 and photoresist and pattern).dm.	US-PGPUB	OR	ON	2008/04/15 09:26
L7	13	((etch\$4 with gas) and ((liquid adj crystal) and expos\$4 and photoresist and pattern).dm.	US-PGPUB	OR	ON	2008/04/15 09:26
S48	927	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:31
S49	963	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S50	27	cutting-off adj plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 14:54

S51	4883	expos\$4 near10 pad near10 etch\$4	US-PGRUB; USPAT; USOCR; EPO; JFO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:38
S52	237	{expos\$4 near10 pad near10 etch\$4} and gate and data and semiconductor and pixel and mask\$4	US-PGRUB; USPAT; USOCR; EPO; JFO; DERWENT; IBM_TDB	OR	ON	2005/05/23 11:15
S53	239	("1954691" "2851408" "2867541" "2959483" "3070441" "3108904" "3259782" "3314871" "3360450" "3525679" "3554889" "3665241" "3675063" "3755704" "3789471" "3808048" "3812559" "3855499" "3898146" "3947716" "3970887" "3998678" "4008412" "4075535" "4084942" "4139773" "4141405" "4143292" "4164680" "4168213" "4178531" "4307507" "4350926" "4482447" "4498952" "4507562" "4512912" "4513308" "4540983" "4542038" "4578614" "4588921" "4594527" "4633131" "4647400" "4663559" "4684353" "4684540" "4685996" "4687825" "4687938" "4710765" "4721885" "4728851" "4758449" "4763187" "4780684" "4788472" "4816717" "4818914" "4822466" "4827177" "4835438" "4851254" "4855636" "4857161" "4857799" "4874981" "4882659" "4889690" "4892757" "4899081" "4900584" "4908539" "4923421" "4926056" "4933108" "4940916" "4943343" "4956202" "4956574" "4964946" "4987007" "4990416" "4990766" "4994205" "5007873" "5015912" "5019003" "5036247" "5038070" "5043715" "5054046" "5054047" "5055077" "5055744"	US-PGRUB; USPAT; USOCR	OR	OFF	2005/05/19 16:28

"5057047"	"5063323"
"5063327"	"5064396"
"5066883"	"5075591"
"5075595"	"5075596"
"5079476"	"5085958"
"5089292"	"5089742"
"5089812"	"5090932"
"5098737"	"5101137"
"5101288"	"5103144"
"5103145"	"5117267"
"5117299"	"5119386"
"5123039"	"5124072"
"5124558"	"5126287"
"5129850"	"5132585"
"5132676")	PN. OR
("5136764"	"5138237"
"5140219"	"5141459"
"5141460"	"5142184"
"5142256"	"5142390"
"5144191"	"5148078"
"5148461"	"5150011"
"5150192"	"5151061"
"5153753"	"5153901"
"5155420"	"5156770"
"5157304"	"5157309"
"5162704"	"5166456"
"5173634"	"5173635"
"5173697"	"5180951"
"5183529"	"5185178"
"5186670"	"5187578"
"5191217"	"5192240"
"5194780"	"5199917"
"5199918"	"5201992"
"5202571"	"5203731"
"5204021"	"5204581"
"5205770"	"5209687"
"5210430"	"5210462"
"5212426"	"5213712"
"5214346"	"5214347"
"5214416"	"5220725"
"5227699"	"5228877"
"5228878"	"5229331"
"5229682"	"5231606"
"5232549"	"5233263"
"5235244"	"5236545"
"5242620"	"5243252"
"5250451"	"5252833"
"5256888"	"5259799"
"5262698"	"5266155"
"5275967"	"5276521"
"5277638"	"5278475"
"5281890"	"5281891"
"5283500"	"5285129"
"5296117"	"5300862"
"5302423"	"5308439"
"5312514"	"5312777"
"5315393"	"5329207"
"5330879"	"5341063"
"5347201"	"5347292"

		"5357172" "5368681" "5378963" "5380546" "5387844" "5393647" "5396150" "5399238" "5401676" "5402041" "5404070" "5408161" "5410218" "5412285" "5473218").PN.				
S54	24	(expos\$4 near10 pad near10 (dry adj etch\$4)) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 16:29
S55	94	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S56	2	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S57	998	349/143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S58	367	349/150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S59	1653	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:25
S60	357	349/43 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S61	73	349/150 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S62	131	349/152 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32

S63	114	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S65	84	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S67	66	349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S69	291	349/43 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:39
S70	111	((expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:08
S71	9	((expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal) and ((three "3") adj mask \$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:54
S72	1857216	(dry adj etch\$4) nea10 insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:11
S73	4990943	S72 (liquid adh crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S74	2348219	S72 (liquid adh crystal) and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S75	150088	(dry adj etch\$4) nea10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15

S76	11537	S75 and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:12
S77	2992	(S75 near10 remov\$4)and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S78	833	(S75 near10 remov\$4)and (liquid adj crystal) and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S79	228	(S75 near10 remov\$4)and (liquid adj crystal) and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:14
S80	1281	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15
S81	40	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4 and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:16
S82	401	349/43 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S83	155	349/152 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S84	96	349/143 and pad and expos \$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S85	86	349/150 and pad and expos \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33

S86	80	349/152 and pad and expos \$4 and mask\$4	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S88	146	349/143 and pad and expos \$4	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S89	425	349/43 and pad and expos \$4	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S90	1193	349/187	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S91	1096	349/187 and @ad< "20031117"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S92	493	349/187 and @ad< "20031117" and mask	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:34
S93	508	349/187 and @ad< "20031117" and mask\$4	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:36
S94	605	"349"/\$.ccls. and @ad< "20031117" and mask\$4 and gate and data and pad and pixel	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:41
S95	104	"349"/\$.ccls. and @ad< "20031117" and mask\$4 and gate and data and pad and pixel and {(thin adj film adj transistor adj array)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:16
S96	565	"349"/\$.ccls. and @ad< "20031117" and mask\$4 and gate and data and pad and pixel and {(thin adj film adj transistor adj array) TFT)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:21

S97	67	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and (((thin adj film adj transistor adj array) TFT) and (cut\$4 near10 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:55
S98	22	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and (((thin adj film adj transistor adj array) TFT) and (cut\$4 near10 off) and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:56
S99	129454	((protect\$4 passivation) near10 substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:22
S100	8486	S99 and (liquid adj crystal) and (mask cutt\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:25
S101	3687	S100 and gate and data	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:24
S102	3387	S100 and gate and data and pixel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:25
S103	13	S99 and (liquid adj crystal) and mask and cutt\$4-off	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S104	7424	S99 and (liquid adj crystal) and mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26

S105	2114	S99 and (liquid adj crystal) and mask and pad	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S106	1031	S99 and (liquid adj crystal) and mask and pad and cut \$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S107	930	S99 and (liquid adj crystal) and mask and pad and cut \$4 and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:27
S108	405	S99 and (liquid adj crystal) and (mask with process) and pad and cut\$4 and etch \$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:29
S109	19	S99 and (liquid adj crystal) and (mask with process) and pad and (cut\$4 with plate) and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:28
S110	261	S99 and (liquid adj crystal) and (mask with process) and pad and cut\$4 and etch \$4 and @ad< "20031117"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:29
S111	28	cutting-off adj plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 16:01
S112	7430	pixel near10 drain near10 contact	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:14
S113	3150	(pixel near10 drain near10 contact) and "349"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:15

S114	2662	((pixel near10 drain near10 (contact adj hole)) and "349"/\$.cds.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 15:16
S115	1126	((pixel near10 drain near10 (contact adj hole)) and "349"/\$.cds.	USPAT	OR	ON	2007/11/20 15:17
S116	1087	((pixel adj electrode) near10 drain near10 (contact adj hole)) and "349"/\$.cds.	USPAT	OR	ON	2007/11/20 15:17
S117	265	((pixel adj electrode) near10 drain near10 (contact adj hole)) and direct and "349"/\$.cds.	USPAT	OR	ON	2007/11/20 15:25
S118	0	((pixel adj electrode) near10 drain near10 (connect with direct)) and "349"/\$.cds.	USPAT	OR	ON	2007/11/20 15:26
S119	279	((pixel adj electrode) near10 drain near10 connect) and "349"/\$.cds.	USPAT	OR	ON	2007/11/20 15:47
S120	21	((pixel adj electrode) near10 drain near10 connect) and "349"/\$.cds. and (without near10 hole)	USPAT	OR	ON	2007/11/20 15:48
S121	28	cutting-off adj plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 16:01
S122	332	((cutting-off) near10 plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/20 16:02
S123	1	((expos\$4 near10 pad near10 (etch\$4 adj gas)) and gate and data and (photoresist adj pattern)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:34
S124	13182	((etch\$4 adj gas) and (dry adj etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:36

S125	2861	{etch\$4 adj gas) and (dry adj etch\$4) and (liquid adj crystal)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:36
S126	2203	{etch\$4 adj gas) and (dry adj etch\$4) and (liquid adj crystal) and expos\$4 and pattern	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:36
S127	372	{etch\$4 adj gas) and (dry adj etch\$4) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:37
S128	247	{etch\$4 adj gas) and (dry adj etch\$4) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and @ad< "20031117"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 11:38
S129	1	"20040125309".pn.	US-PGRUB	OR	ON	2008/02/28 11:58
S130	120	((etch\$4 adj gas) near10 (dry adj etch\$4)) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and @ad< "20031117"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/28 12:02
S131	120	((etch\$4 adj gas) near10 (dry adj etch\$4)) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and @ad< "20031117"	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 16:05
S132	56	((etch\$4 adj gas) near10 (dry adj etch\$4)) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and @ad< "20031117" and pass\$4	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 16:27
S133	56	((etch\$4 adj gas) near10 (dry adj etch\$4)) and (liquid adj crystal) and expos\$4 and (photoresist adj pattern) and (@ad< "20031117" @ad= "20031117") and pass\$4	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 17:11

4/ 15/ 08 10:11:15 AM

C:\Documents and Settings\MQ\My Documents\EAST\workspaces\10713198
[cutting_off_plate_dry_etching].wsp